

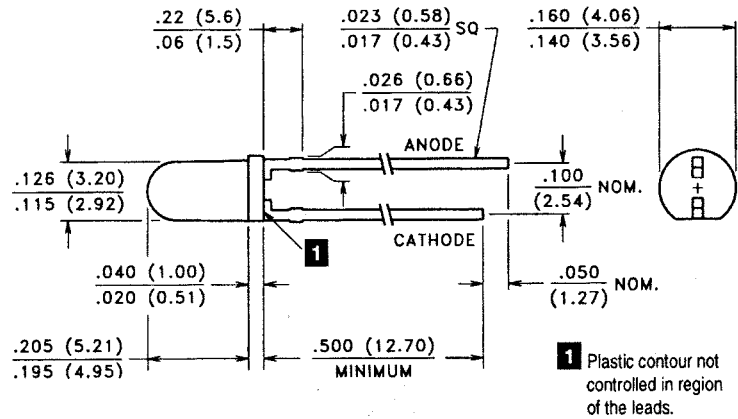
GaAlAs Infrared Emitting Diodes

Long T-1 (3 mm) Plastic Package — 880 nm

VTE3372LA, 74LA



PACKAGE DIMENSIONS inch (mm)



CASE 50A Long T-1 (3 mm)

CHIP SIZE: .011" x .011"

DESCRIPTION

This narrow beam angle 3 mm diameter plastic packaged emitter is suitable for use in optical switch applications. It contains a small area, GaAlAs, 880 nm, high efficiency IRED die.

ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures										
Storage and Operating:	-40°C to 100°C	Maximum Reverse Voltage:	5.0V							
Continuous Power Dissipation:	100 mW	Maximum Reverse Current @ $V_R = 5V$:	10 μA							
Derate above 30°C:	1.43 mW/°C	Peak Wavelength (Typical):	880 nm							
Maximum Continuous Current:	50 mA	Junction Capacitance @ 0V, 1 MHz (Typ.):	14 pF							
Derate above 30°C:	0.71 mA/°C	Response Time @ $I_F = 20$ mA								
Peak Forward Current, 10 μs , 100 pps:	2.5 A	Rise: 1.0 μs Fall: 1.0 μs								
Temp. Coefficient of Power Output (Typ.):	-8%/°C	Lead Soldering Temperature:	260°C							
		(1.6 mm from case, 5 seconds max.)								

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

Part Number	Output						Forward Drop		Half Power Beam Angle	
	Irradiance		Radiant Intensity	Total Power	Test Current	V_F				
	E_e	Condition		I_e	P_O	I_{FT}	@ I_{FT}	$\theta_{1/2}$		
	mW/cm ²	distance	Diameter	mW/sr	mW	mA	Volts			
	Min.	Typ.	mm	mm	Min.	Typ.	(Pulsed)	Typ.	Max.	Typ.
VTE3372LA	2.0	2.6	10.16	2.1	2.0	3.0	20	1.3	1.8	$\pm 10^\circ$
VTE3374LA	4.0	5.2	10.16	2.1	4.1	5.0	20	1.3	1.8	$\pm 10^\circ$

■ Refer to General Product Notes, page 2.

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nordics@amstechnologies.com
azpect.amstechnologies.com

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